

Notice of References Cited	Application/Control No. 10/749,771	Applicant(s)/Patent Under Reexamination SHYU ET AL.	
	Examiner Evan Pert	Art Unit 2826	Page 1 of 1

U.S. PATENT DOCUMENTS

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Name	Classification
	A	US-2003/0123216 A1	07-2003	Yoon et al.	361/303
	B	US-6,025,245 A	02-2000	Wei, Houngh-Chi	438/386
	C	US-5,142,438 A	08-1992	Reinberg et al.	361/313
	D	US-			
	E	US-			
	F	US-			
	G	US-			
	H	US-			
	I	US-			
	J	US-			
	K	US-			
	L	US-			
	M	US-			

FOREIGN PATENT DOCUMENTS

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Country	Name	Classification
	N	EP 0 980 100 A2	02-2000	EPO	Bronner et al.	H01L 27/108
	O					
	P					
	Q					
	R					
	S					
	T					

NON-PATENT DOCUMENTS

*		Include as applicable: Author, Title Date, Publisher, Edition or Volume, Pertinent Pages)
	U	Senzaki et al., "Atomic Layer Deposition of High-k Thin Films for Gate and Capacitor Dielectrics," 2004 International Conference on Integrated Circuit Design and Technology, pages 269-274.
	V	Gutsche et al., "Capacitance Enhancement Techniques for Sub-100nm Trench DRAMs", December 2001, Electron Devices meeting 2001 IEDM technical Digest, pages 18.6.1-18.6.4.
	W	
	X	

*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)
Dates in MM-YYYY format are publication dates. Classifications may be US or foreign.